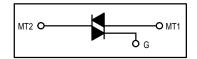
# **Triacs**

# **Silicon Bidirectional Thyristors**

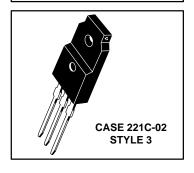
... designed primarily for full-wave ac control applications, such as solid-state relays, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied anode voltage with positive or negative gate triggering.

- Blocking Voltage to 800 Volts
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Three Modes (MAC320FP Series) or Four Modes (MAC320AFP Series)



# MAC320FP Series MAC320AFP Series

ISOLATED TRIACS THYRISTORS 20 AMPERES RMS 200 thru 800 VOLTS



#### **MAXIMUM RATINGS** (T<sub>C</sub> = 25°C unless otherwise noted.)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage <sup>(1)</sup> (T <sub>J</sub> = -40 to +125°C, 1/2 Sine Wave 50 to 60 Hz, Gate Open)	V <sub>DRM</sub>		Volts
MAC320-4FP, MAC320A4FP MAC320-6FP, MAC320A6FP MAC320-8FP, MAC320A8FP MAC320-10FP, MAC320A10FP		200 400 600 800	
Peak Gate Voltage	V <sub>GM</sub>	10	Volts
On-State RMS Current (T <sub>C</sub> = +75°C, Full Cycle Sine Wave 50 to 60 Hz) <sup>(2)</sup>	IT(RMS)	20	Amps
Peak Nonrepetitive Surge Current (One Full Cycle, 60 Hz, T <sub>C</sub> = +75°C, preceded and followed by rated current)	ITSM	150	Amps
Peak Gate Power (T <sub>C</sub> = +75°C, Pulse Width = 2 μs)	P <sub>GM</sub>	20	Watts
Average Gate Power (T <sub>C</sub> = +75°C, t = 8.3 ms)	P <sub>G(AV)</sub>	0.5	Watt
Peak Gate Current	l <sub>GM</sub>	2	Amps
RMS Isolation Voltage (T <sub>A</sub> = 25°C, Relative Humidity ≤ 20%)	V(ISO)	1500	Volts
Operating Junction Temperature	TJ	-40 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to +150	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	1.8	°C/W
Thermal Resistance, Case to Sink	$R_{\theta CS}$	2.2 (typ)	°C/W
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	60	°C/W

- 1. V<sub>DRM</sub> for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
- 2. The case temperature reference point for all T<sub>C</sub> measurements is a point on the center lead of the package as close as possible to the plastic body.



**ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$  unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
Peak Blocking Current (VD = Rated VDRM, Gate Open)  TJ = 25°C  TJ = +125°C	IDRM	_	_	10 2	μΑ mA
Peak On-State Voltage (Either Direction) (I <sub>TM</sub> = 28 A Peak; Pulse Width = 1 to 2 ms, Duty Cycle ≤ 2%)	V <sub>TM</sub>	_	1.4	1.7	Volts
Peak Gate Trigger Current (Main Terminal Voltage = 12 Vdc, R <sub>L</sub> = 100 Ohms Minimum Gate Pulse Width = 2 μs) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY	lGT	  -  -  -	_ _ _ _	50 50 50 75	mA
Peak Gate Trigger Voltage (Main Terminal Voltage = 12 Vdc, $R_L$ = 100 Ohms Minimum Gate Pulse Width = 2 $\mu$ s) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY (Main Terminal Voltage = Rated VDRM, $R_L$ = 10 , $T_J$ = +110°C) MT2(+), G(+); MT2(+), G(-) MT2(-), G(-); MT2(-), G(+) "A" SUFFIX ONLY	V <sub>GT</sub>		0.9 0.9 1.1 1.4	2 2 2 2.5 —	Volts
Holding Current (Either Direction) (Main Terminal Voltage = 12 Vdc, Gate Open, Initiating Current = 200 mA)	lН	_	6	40	mA
Turn-On Time ( $V_D$ = Rated $V_{DRM}$ , $I_{TM}$ = 28 A, $I_{GT}$ = 120 mA, Rise Time = 0.1 $\mu$ s, Pulse Width = 2 $\mu$ s)	tgt		1.5	10	μs
Critical Rate of Rise of Commutation Voltage ( $V_D$ = Rated $V_{DRM}$ , $I_{TM}$ = 28 A, Commutating di/dt = 10 A/ms, Gate Unenergized, $T_C$ = +75°C)	dv/dt(c)		5	_	V/μs

# TYPICAL CHARACTERISTICS

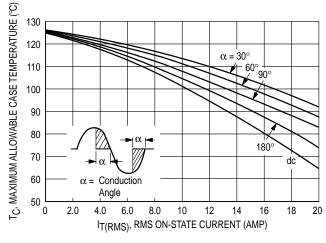


Figure 1. RMS Current Derating

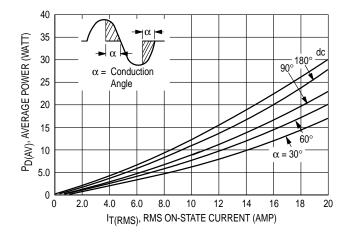


Figure 2. On-State Power Dissipation

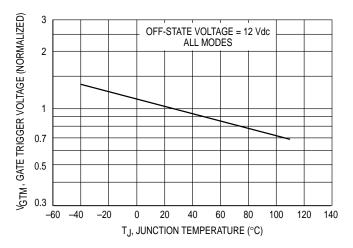


Figure 3. Typical Gate Trigger Voltage

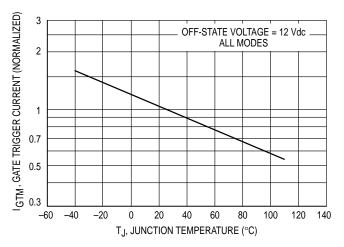


Figure 4. Typical Gate Trigger Current

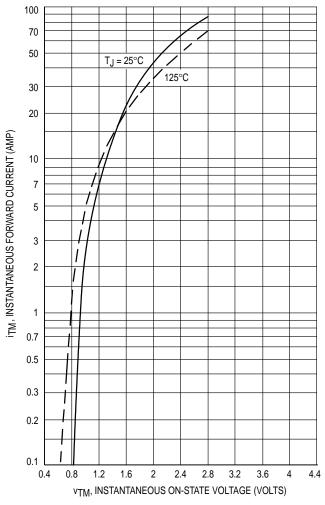
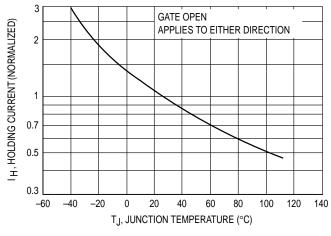


Figure 5. Maximum On-State Characteristics



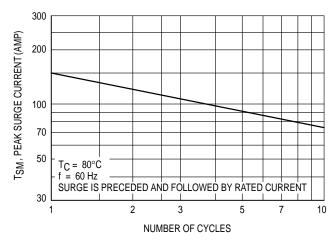


Figure 6. Typical Holding Current

Figure 7. Maximum Nonrepetitive Surge Current

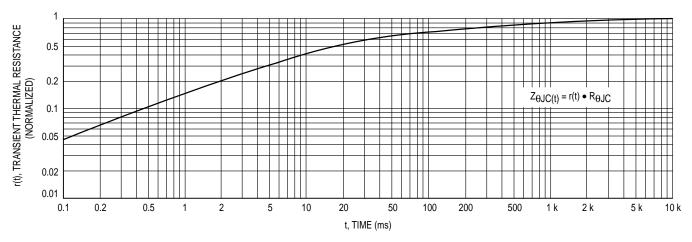
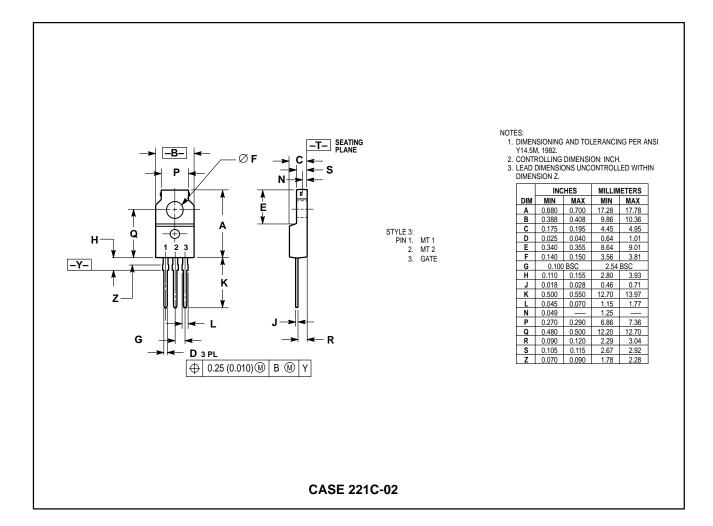


Figure 8. Thermal Response

### **PACKAGE DIMENSIONS**



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